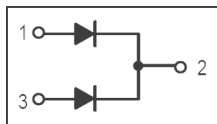
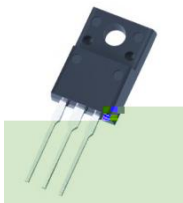


TO-220F

Ultrafast Recovery Diode in a TO-220F Plastic Package.

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

For high frequency, high voltage, high current rectifier diode, freewheeling diode



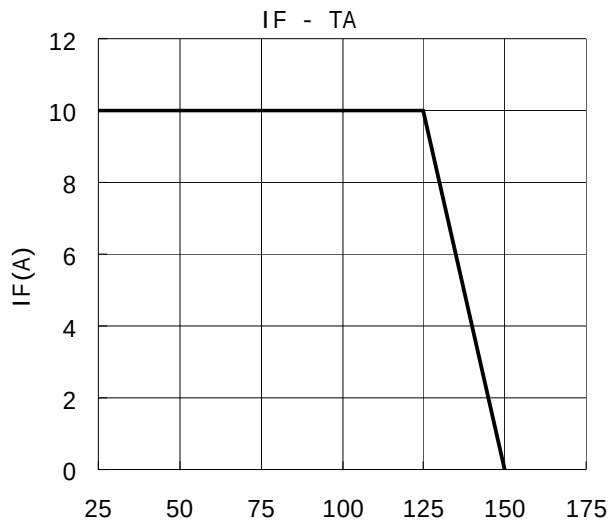
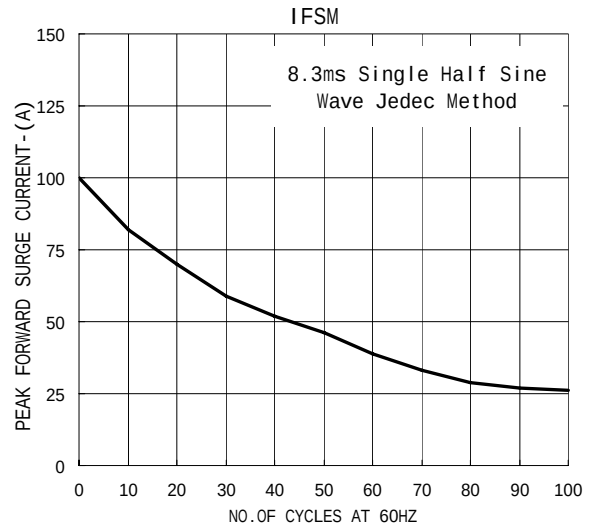
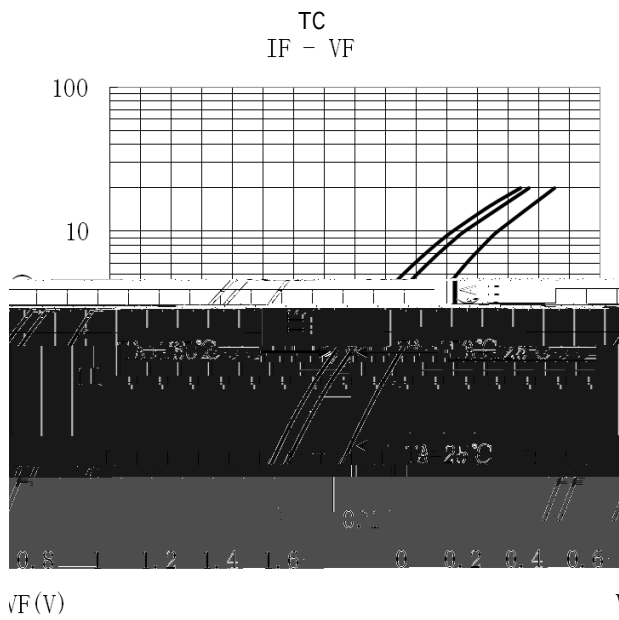
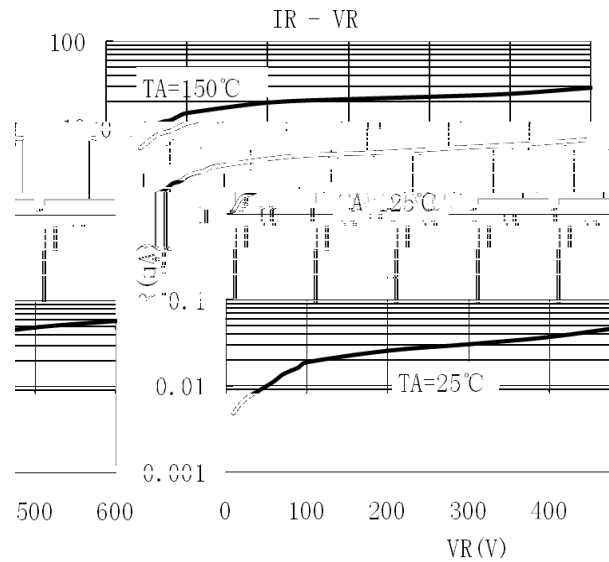
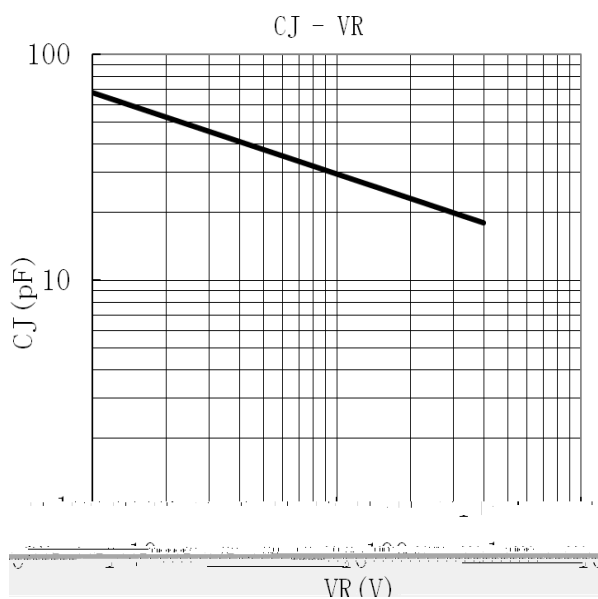
PIN1 Anode PIN2 Cathode PIN3 Anode

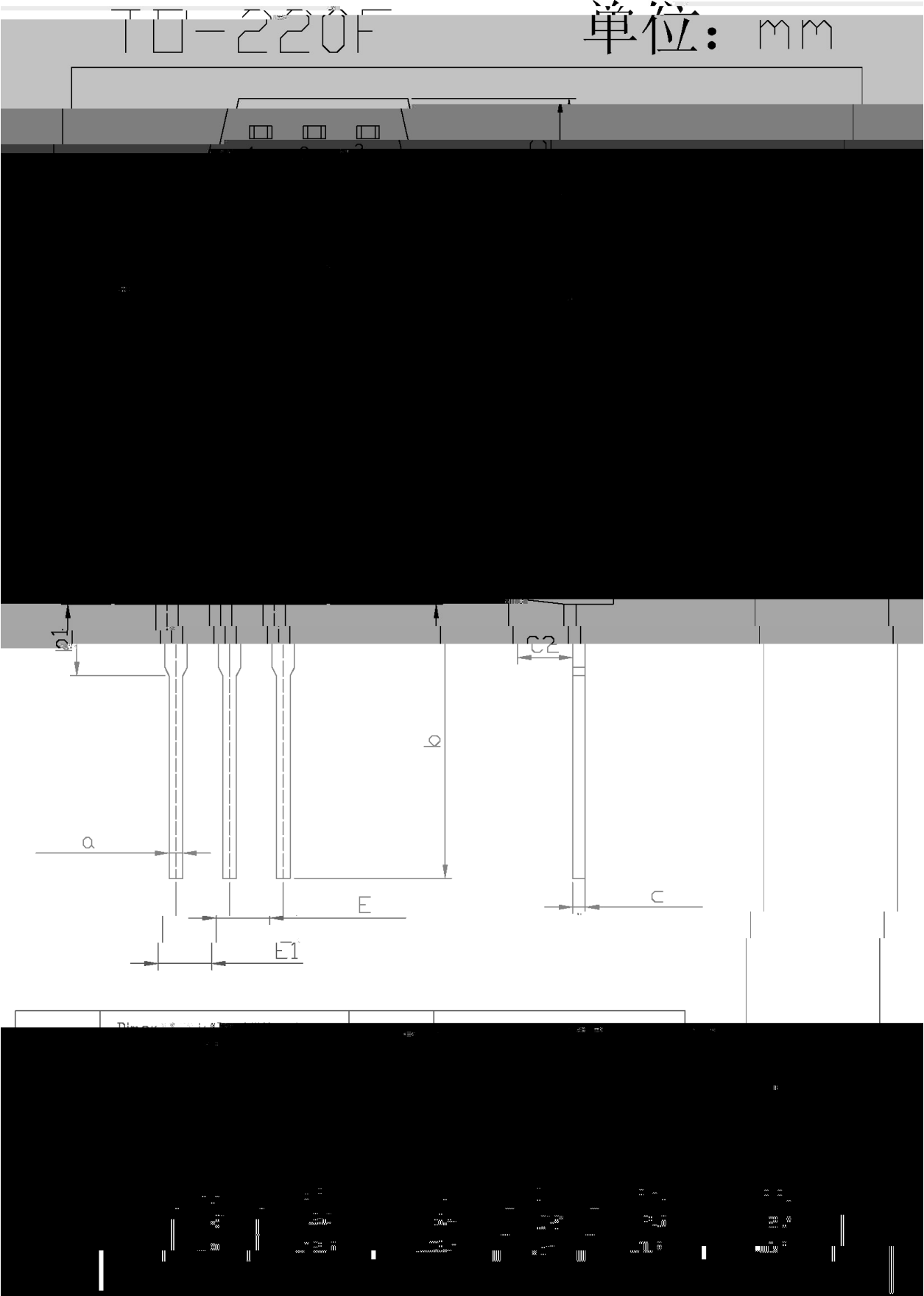
See Marking Instructions

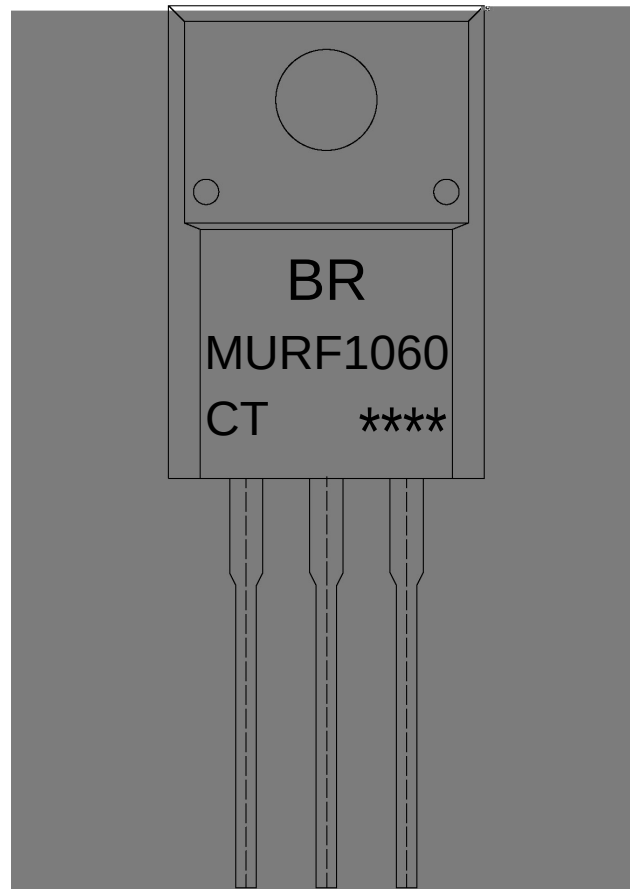
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Reverse Voltage	V_{RMS}	420	V
DC Blocking Voltage	V_{DC}	600	V
Forward Current	I_F	2×5	A
Peak forward surge current	I_{FSM}	100	A
Typical Thermal Resistance Junction to Case	$R_{\theta Jc}$	4	/W
Junction Temperature Range	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R=1mA$	600			V
Forward Voltage	V_F	$I_F=1A \quad T_C=25$		0.91	1.05	V
		$I_F=1A \quad T_C=125$		0.74	0.95	
		$I_F=5A \quad T_C=25$		1.15	1.5	
		$I_F=5A \quad T_C=125$		1.0	1.2	

Instantaneous Reverse Current I_R







BR

MURF1060

CT:

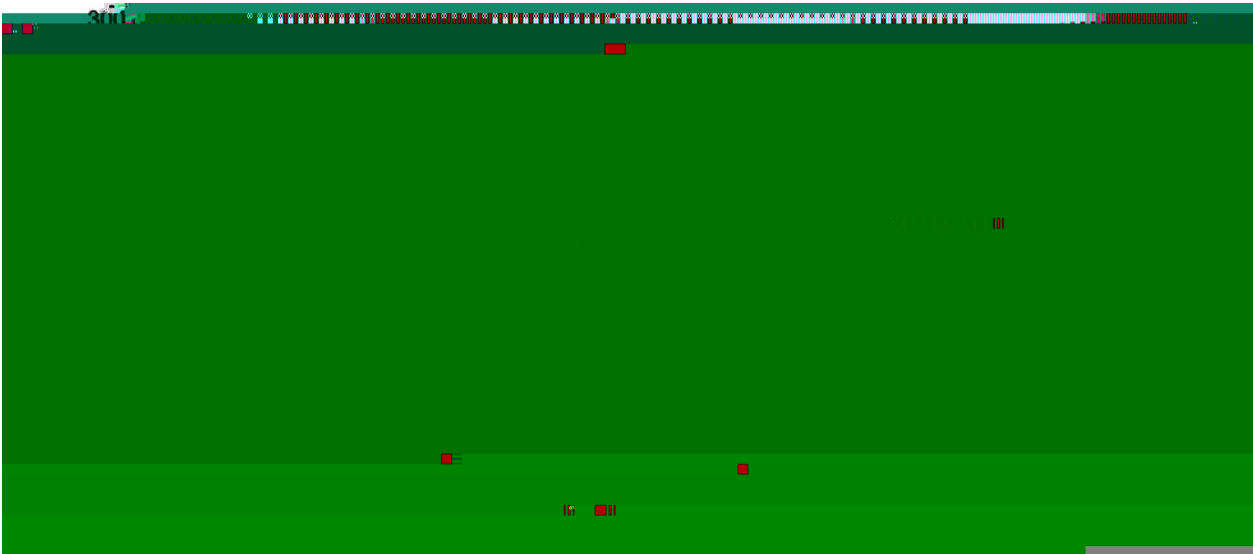
Note:

BR: Company Code

MURF1060 Product Type.

CT: Internal Structure

****: Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;

2

255±5

5±0.5sec;

3

2 10

/sec.
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type	Units		Dimension		(unit mm ³)
	Units/Bag	Bags/Inner Box	Units/Inner Box	Units/Inner Box	